

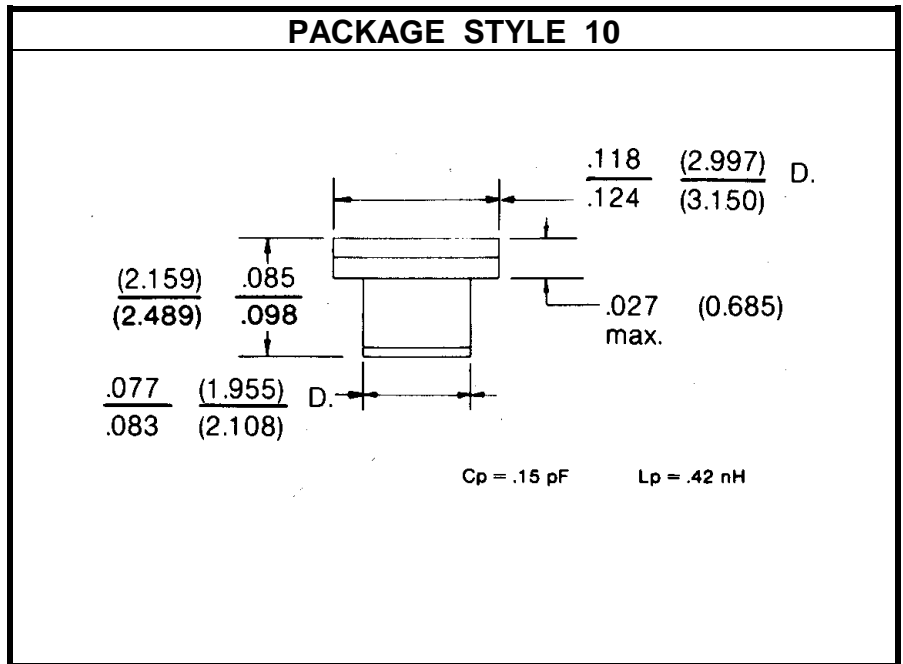
SILICON ABRUPT JUNCTION TUNING VARACTOR

DESCRIPTION:

The **AT6019-10** is an Epitaxial Silicon Abrupt Junction Microwave Tuning Varactor. This Device is Passivated With Silicon Dioxide Which Results in Very Low Leakage Current. The Capacitance Voltage Relationship Closely Approximates Square Law ($n = 0.5$).

MAXIMUM RATINGS

I_C	100 mA
V_{CE}	60 V
P_{DISS}	250 mW @ T _C = 25 °C
T_J	-65 °C to +150 °C
T_{STG}	-65 °C to +150 °C


CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
V_B	I _R = 10 μA	60			V
C_T	V _R = 4.0 V	29.70	33.00	36.30	pF
ΔC_T	C _T = 0 V / C _T = 8.0 V	7.4			RATIO
Q	V _R = 4.0 V	700			---
T_C	V _R = 4.0 V			300	Ppm/°C